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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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2SA1083, 2SA1084, 2SA1085

Silicon PNP Epitaxial

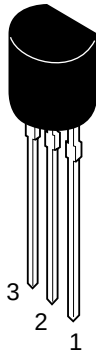
RENESAS

Application

- Low frequency low noise amplifier
- Complementary pair with 2SC2545, 2SC2546 and 2SC2547

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SA1083, 2SA1084, 2SA1085

Absolute Maximum Ratings (Ta = 25°C)

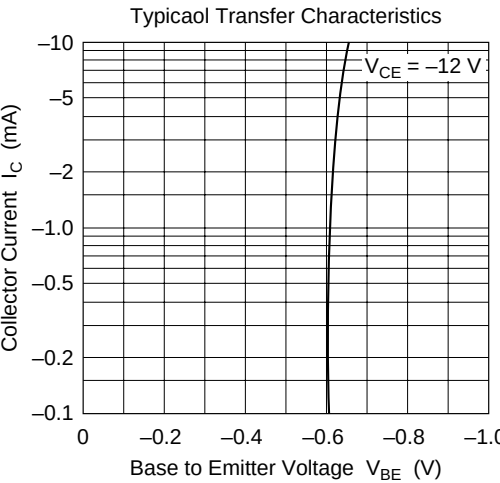
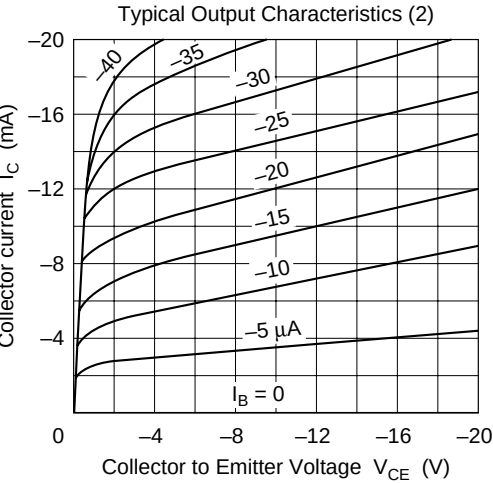
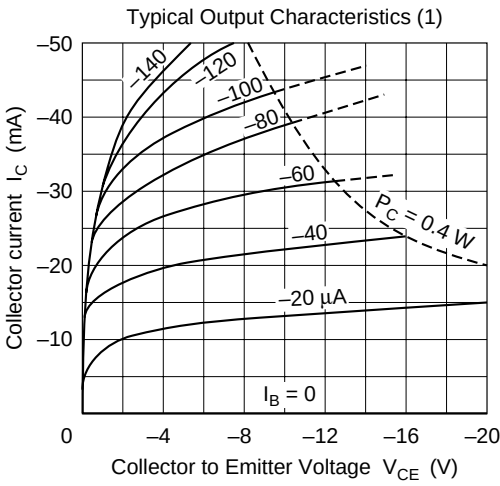
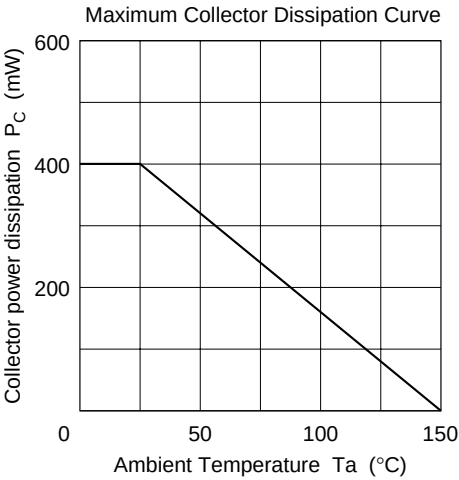
Item	Symbol	2SA1083	2SA1084	2SA1085	Unit
Collector to base voltage	V _{CBO}	−60	−90	−120	V
Collector to emitter voltage	V _{CEO}	−60	−90	−120	V
Emitter to base voltage	V _{EBO}	−5	−5	−5	V
Collector current	I _C	−100	−100	−100	mA
Emitter current	I _E	100	100	100	mA
Collector power dissipation	P _C	400	400	400	mW
Junction temperature	T _j	150	150	150	°C
Storage temperature	T _{stg}	−55 to +150	−55 to +150	−55 to +150	°C

Electrical Characteristics (Ta = 25°C)

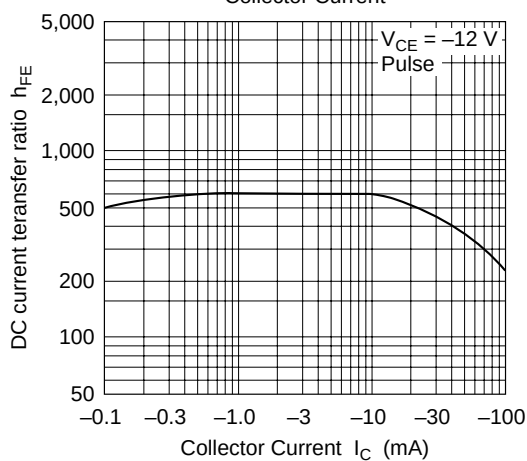
Item	Symbol	2SA1083			2SA1084			2SA1085			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-60	—	—	-90	—	—	-120	—	—	V	$I_C = -10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60	—	—	-90	—	—	-120	—	—	V	$I_C = -1\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	-5	—	—	V	$I_E = -10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-0.1	—	—	-0.1	—	—	-0.1	μA	$V_{CB} = -50\text{ V}$, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-0.1	—	—	-0.1	—	—	-0.1	μA	$V_{EB} = -2\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	250	—	800	250	—	800	250	—	800		$V_{CE} = -12\text{ V}$, $I_C = -2\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.2	—	—	-0.2	—	—	-0.2	V	$I_C = -10\text{ mA}$, $I_B = -1\text{ mA}$
Base to emitter voltage	V_{BE}	—	-0.6	—	—	-0.6	—	—	-0.6	—	V	$V_{CE} = -12\text{ V}$, $I_C = -2\text{ mA}$
Gain bandwidth product	f_T	—	90	—	—	90	—	—	90	—	MHz	$V_{CE} = -12\text{ V}$, $I_C = -2\text{ mA}$
Collector output capacitance	C_{ob}	—	3.5	—	—	3.5	—	—	3.5	—	pF	$V_{CB} = -10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$
Noise voltage referred to input	e_n	—	0.5	—	—	0.5	—	—	0.5	—	nV/ $\sqrt{\text{Hz}}$	$V_{CE} = -6\text{ V}$, $I_C = -10\text{ mA}$, $f = 1\text{ kHz}$, $R_g = 0$, $\Delta f = 1\text{ Hz}$

Note: 1. The 2SA1083, 2SA1084 and 2SA1085 are grouped by h_{FE} as follows.

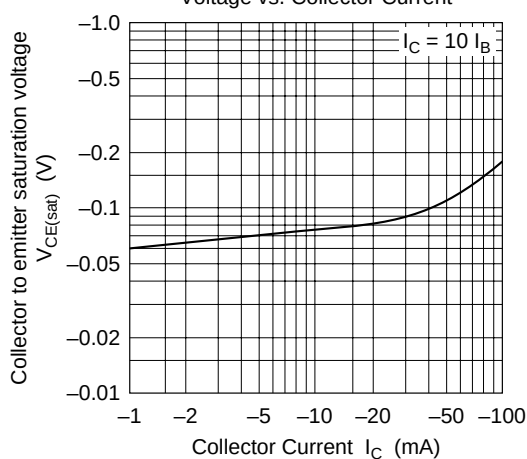
D	E
250 to 500	400 to 800



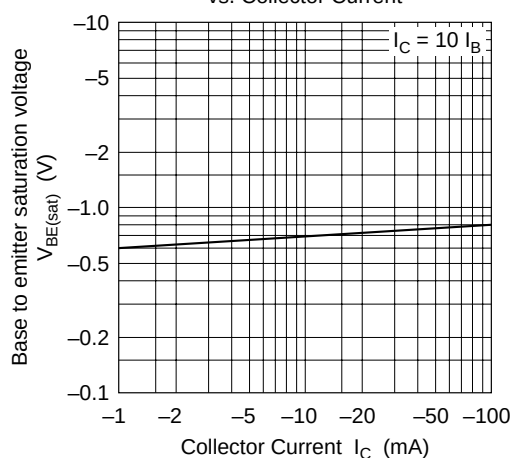
DC Current Transfer Ratio vs.
Collector Current



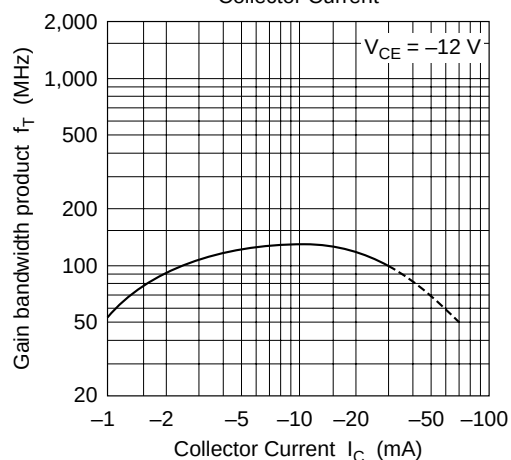
Collector to Emitter Saturation
Voltage vs. Collector Current



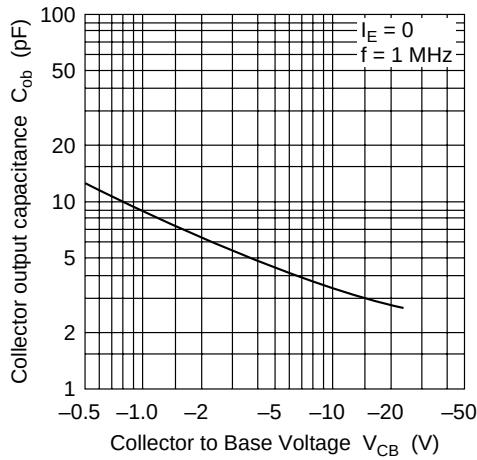
Base to Emitter Saturation Voltage
vs. Collector Current



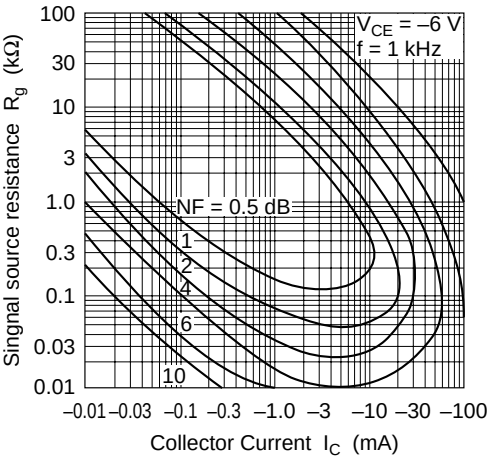
Gain Bandwidth Product vs.
Collector Current



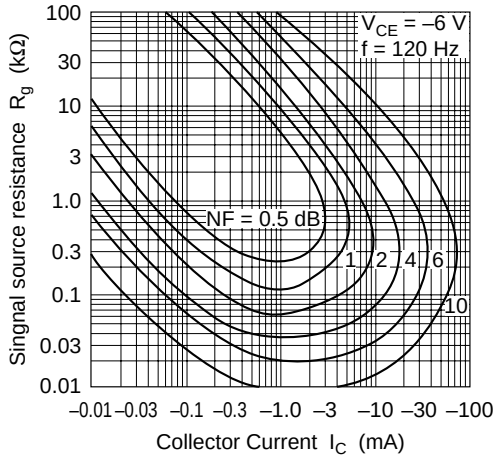
Collector Output Capacitance vs.
Collector to Base Voltage



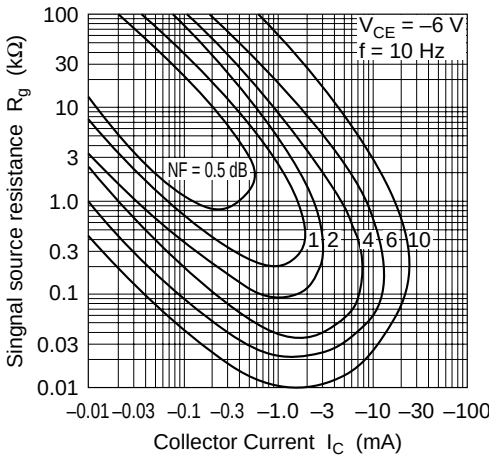
Contours of Constant Noise Figure (1)



Contours of Constant Noise Figure (2)



Contours of Constant Noise Figure (3)



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan

Tel: Tokyo (03) 3270-2111

Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.

Semiconductor & IC Div.

2000 Sierra Point Parkway

Brisbane, CA. 94005-1835

U S A

Tel: 415-589-8300

Fax: 415-583-4207

Hitachi Europe GmbH

Electronic Components Group

Continental Europe

Dornacher Straße 3

D-85622 Feldkirchen

München

Tel: 089-9 91 80-0

Fax: 089-9 29 30 00

Hitachi Europe Ltd.

Electronic Components Div.

Northern Europe Headquarters

Whitebrook Park

Lower Cookham Road

Maidenhead

Berkshire SL6 8YA

United Kingdom

Tel: 0628-585000

Fax: 0628-778322

Hitachi Asia Pte. Ltd.

16 Collyer Quay #20-00

Hitachi Tower

Singapore 0104

Tel: 535-2100

Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.

Unit 706, North Tower,

World Finance Centre,

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon

Hong Kong

Tel: 27359218

Fax: 27306071